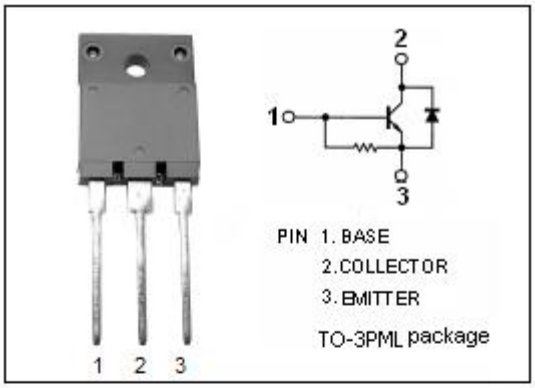
isc Silicon NPN Power Transistor — 2SC5480

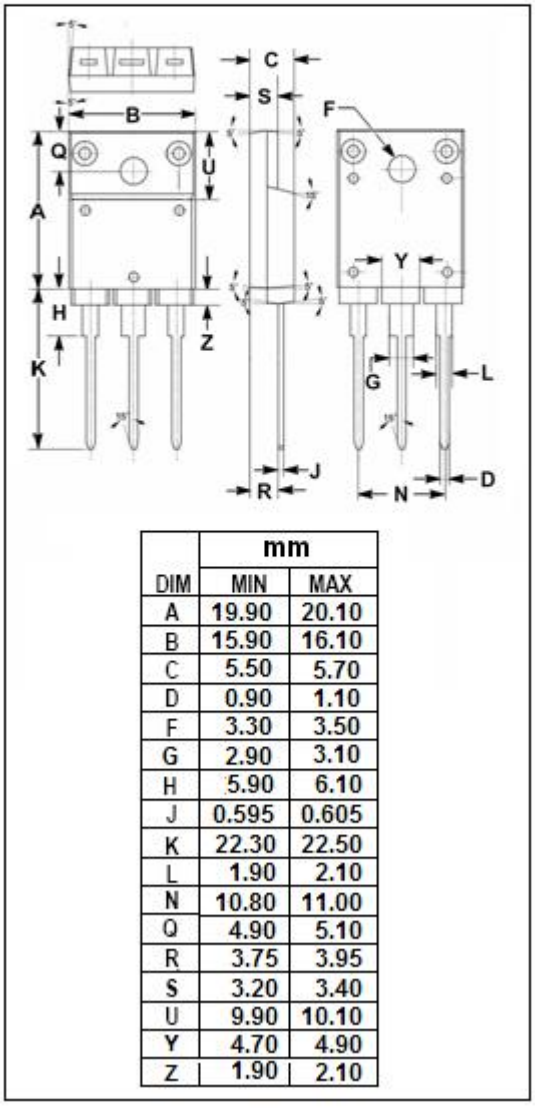


DESCRIPTION

- High Breakdown Voltage-
  : V_{CBO}= 1500V (Min)
- High Switching Speed
- Built-in Damper Diode
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Designed for horizontal deflection output stage applications.



DIM	mm MIN	mm MAX
A	19.90	20.10
B	15.90	16.10
C	5.50	5.70
D	0.90	1.10
F	3.30	3.50
G	2.90	3.10
H	5.90	6.10
J	0.595	0.605
K	22.30	22.50
L	1.90	2.10
N	10.80	11.00
Q	4.90	5.10
R	3.75	3.95
S	3.20	3.40
U	9.90	10.10
Y	4.70	4.90
Z	1.90	2.10

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CES}	Collector-Emitter Voltage	1500	V
V_{EBO}	Emitter-Base Voltage	5	V
$I_{C(peak)}$	Collector Current-Peak	14	A
$I_{C(surge)}$	Collector Current-Surge	28	A
P_C	Collector Power Dissipation @ T_C=25℃	50	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E= 500mA; I_C= 0	5			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 10A; I_B= 2.5A			5.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= 10A; I_B= 2.5A			1.5	V
I_{CES}	Collector Cutoff Current	V_{CE}= 1500V; R_{BE}= 0			500	μA
h_{FE-1}	DC Current Gain	I_C= 1A; V_{CE}= 5V	5		25	
h_{FE-2}	DC Current Gain	I_C= 10A; V_{CE}= 5V	4		7	
t_f	Fall Time	I_{CP}= 7A, I_{B1}= 2.4A; f_H= 31.5kHz			0.4	μs